

# High-Speed Switching Power Supply Using SiC RESURF JFETs

Satoshi HATSUKAWA\*, Takashi TSUNO, Kazuhiro FUJIKAWA, Nobuo SHIGA, Tuya WUREN, Kazuyuki WADA and Takashi OHIRA

We have developed a Silicon Carbide (SiC) junction field effect transistor (JFET) with a reduced surface field (RESURF) structure. This JFET is 2 mm × 2 mm in size and has good characteristics for high speed switching: a normal saturation current of about 250 A/cm<sup>2</sup> at a gate voltage of 2 V, a specific on-resistance of about 13 mΩ cm<sup>2</sup>, and a maximum blocking voltage of over 250 V. Using this JFET, we have developed a novel harmonic canceling switch array (HCA) circuit which combines phase shifted signal and demonstrated pulse width modulation (PWM). The carrier wave of 20.5 MHz, which was pulse-width modulated with a 4.1 MHz input signal, was successfully demodulated.

Keywords: RESURF JFET, high temperature characteristics, DC-DC converter, 4H-SiC

## 1. Introduction

In the use of electrical energy, conversions and control technologies are important. Power electronics equipment, including inverters, DC-DC converters, and switching regulators, are used to convert and control electrical energy efficiently. Transistors, thyristors, and other switching semiconductor devices are placed at the core of these equipment units.

High efficiency and compactness are in high demand for power electronics equipment. To satisfy these demands, power-switching devices are required to have characteristics for low loss and fast switching. In silicon (Si) power switching devices, the currently used and most popular, the solutions to these requirements are improving device structures, such as bipolar junction transistors (BJTs), gate-turn-off thyristors (GTOs), metal oxide semiconductor field effect transistors (MOSFETs), and insulated gate bipolar transistors (IGBTs), and reducing the size of these devices.

In recent years, the demand for energy efficiency has increased, especially in the face of growing public concern about global warming. Under these circumstances, power electronics equipment is required to use energy more efficiently. However, the characteristics of Si power devices are reaching the physical limits of Si. Power devices of semiconductors better than Si are expected. In particular, silicon carbide (SiC) power devices, a kind of wide bandgap semiconductor, are now attracting a great deal of attention<sup>(1), (2)</sup>.

SiC keeps its physical properties even at high temperatures, where Si cannot work. Therefore, it has great potential as devices used in high temperature environments. SiC power devices with a high operating temperature and low loss make a cooling system simple, and contribute to a reduction in both the size and cost of the entire power system.

We develop a SiC reduced surface field (RESURF) junction field effect transistor (JFET), which is a power switching device. Its structure is suitable for SiC. The applications are supposed to be in power electronics equipment for automotives and other apparatuses for consumer use.

The SiC RESURF JFET has some unique advantages, such as low loss, high operating temperature, and enables high-speed switching operation<sup>(3)-(5)</sup>. Therefore, it is one of the candidate devices for high-speed switching power supply. In this report, we developed a high-speed switching power supply device using a SiC RESURF JFET for amplifying an envelope signal in a pulse width modulation (PWM) form. It can save power consumption effectively for wireless base stations.

## 2. SiC RESURF JFET

Figure 1 shows the top view of the fabricated device. The chip, whose size is 2 mm × 2 mm, consists of 4 transistor units. A transistor unit, whose size is 0.48 mm × 1.9 mm, consists of 100 cells connected in parallel by comb-shaped metal electrodes. The width of the channel of each cell is 150 μm. The total width of the channel in a single chip is about 60 mm.

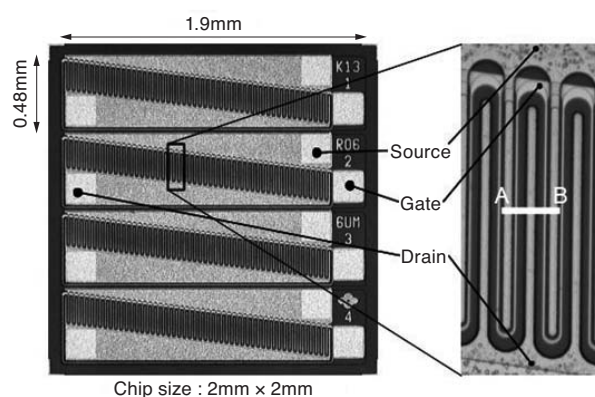
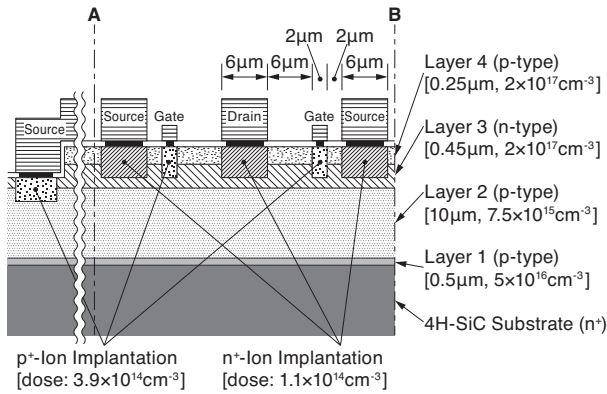


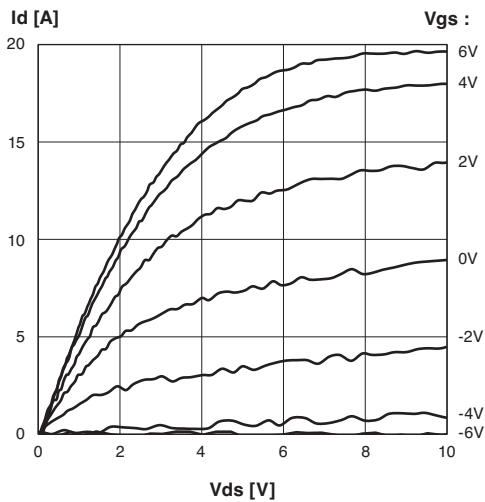
Fig. 1. Top view of SiC RESURF JFET

**Figure 2** shows a schematic cross-sectional view of the fabricated device along a line between points A and B in **Fig. 1**. The drift region, between the drain and the gate areas, has a double RESURF structure, which is composed of epitaxial layers based on the super-junction theory. The epitaxial layers consist of active layers (layers 3 and 4), a depletion layer (layer 2) and a field stop layer (layer 1). The thickness and the dopant concentration of each layer are shown in **Fig. 2**. The drift length, which is the distance between the drain and the gate areas, is  $6\text{ }\mu\text{m}$  for a blocking capability of  $600\text{ V}$ . The channel (gate) length is  $2\text{ }\mu\text{m}$ . The width of the drain and the source fingers is  $6\text{ }\mu\text{m}$ . The pitch of the cells is  $16\text{ }\mu\text{m}$ . JFETs were fabricated on an  $8^\circ$  off (0001)-face  $n^+$ -type 4H-SiC substrate. The details of the fabrication process were described in our former work<sup>(5)</sup>.

**Figure 3** shows the typical on-state characteristics of the fabricated transistor. The device shows the current saturation characteristic of FET. It is confirmed that the gate voltage controls the drain current successfully. The on-resistance is calculated to be  $250\text{ m}\Omega$  from the drain current ( $I_d$ ) when the gate voltage ( $V_{gs}$ ) is  $2\text{ V}$  and the drain voltage ( $V_{ds}$ ) is  $1\text{ V}$ .

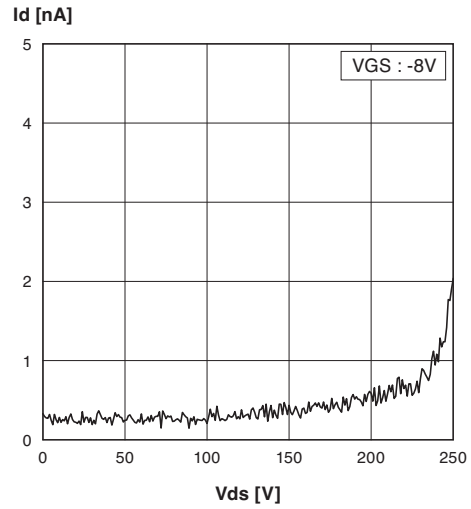


**Fig. 2.** Cross-sectional view of RESURF JFET

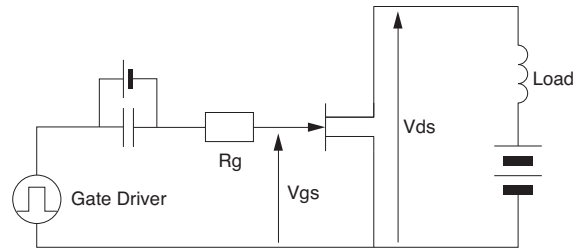


**Fig. 3.** Drain current ( $I_d$ ) versus drain voltage ( $V_{ds}$ ) different values of gate voltage ( $V_{gs}$ )

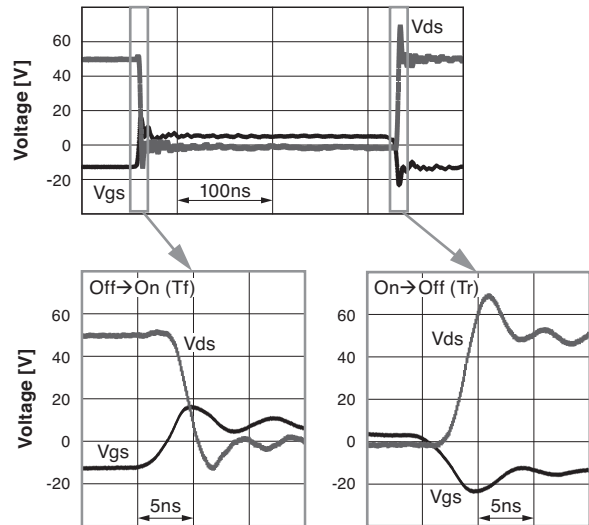
**Figure 4** shows the blocking characteristics of the fabricated transistor. The gate voltage ( $V_{gs}$ ) is  $-8\text{ V}$ , at which the transistor turns off. The transistor has a measured blocking voltage of more than  $250\text{ V}$ .



**Fig. 4.** Blocking characteristics



**Fig. 5.** Evaluation circuit for measuring inductive load switching characteristics



**Fig. 6.** Switching characteristics

Figure 5 shows the testing circuit of switching characteristics. Figure 6 shows the typical switching waveforms of drain voltage ( $V_{ds}$ ) and gate voltage ( $V_{gs}$ ) for an inductive load. Turn-on and turn-off time are about 2 ns, respectively.

### 3. Principle of the Power Supply Circuit

#### 3-1 Envelope elimination and restoration

Envelope Elimination and Restoration (EER) techniques have been proposed for improving the efficiency of power amplifiers. It is an efficient circuit, which performs power amplification only by switching, without using a high frequency linear amplifier. Those signals are combined, after an input radio frequency (RF) signal is resolved into an envelope signal and a phase signal. Figure 7 shows a schematic of EER. The envelope signal is changed into a pulse width modulated (PWM) signal and is amplified keeping linearity. Since PWM signals have high frequency and high voltage, a practical circuit has not been realized with conventional silicon devices.

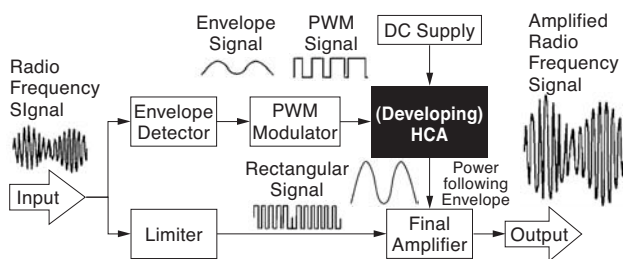


Fig. 7. Schematic of EER

#### 3-2 Distributed amplifier and low pass filter

Figure 8 shows a distributed amplifier circuit and a low pass filter. Our former work incorporates transmission line theory into the distributed amplifier to obtain a larger gain-bandwidth product. However, this circuit wastes power due to the matching resistor at its output.

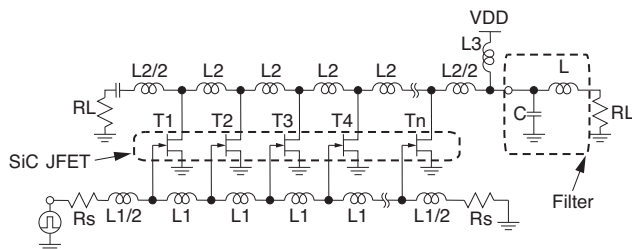


Fig. 8. Distributed amplifier and low pass filter

#### 3-3 Harmonic Canceling switch Array (HCA)

We devised a novel HCA shown in Fig. 9. Although it has neither a terminator nor a low pass filter, it can demodulate PWM signals. As shown in Fig. 9, signals which have different phases each other are fed into each JFET gate like a distributed amplifier. This configuration can reduce input capacitance at the subcarrier operating frequency and improve the frequency characteristics. The phase difference of the input signals to the adjoining devices is set to  $1/n$  ( $n$  is the number of switching devices) of the subcarrier cycle of the PWM signal. The output signals are composed in-phase to cancel the subcarriers up to  $(n-1)$ -th order harmonics. The calculation results of the frequency component of the output for various numbers of switching devices are shown in Fig. 10.

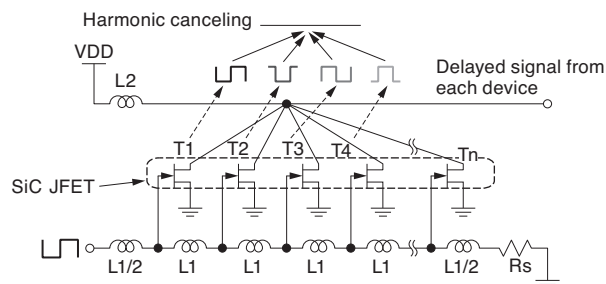


Fig. 9. The principles of Harmonic Canceling switch Array (HCA)

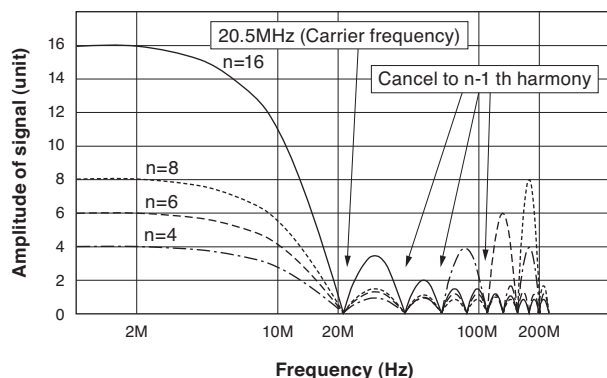


Fig. 10. The frequency characteristic of HCA

### 4. Results

The test circuit of HCA for EER is shown in Fig. 11. Eight SiC JFETs are arranged on an arc so that the in-phase composition can be performed at the center of the arc.

The 4.1 MHz PWM signal with a 20.5 MHz subcarrier is fed at the input of the HCA. The output frequency characteristic of this amplifier is shown in Fig. 12 (a) and the demodulated output is shown in Fig. 12 (b). The 20.5 MHz subcarrier and its 2nd order harmonic are cancelled at the output of the HCA as the dips in Fig. 12 (a) indicate.

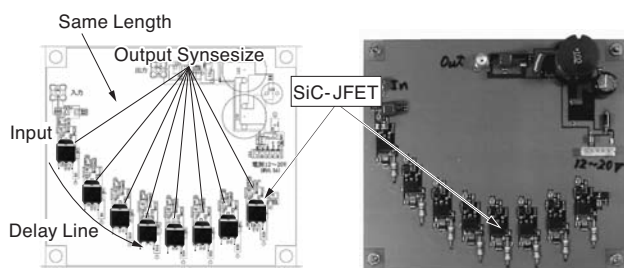
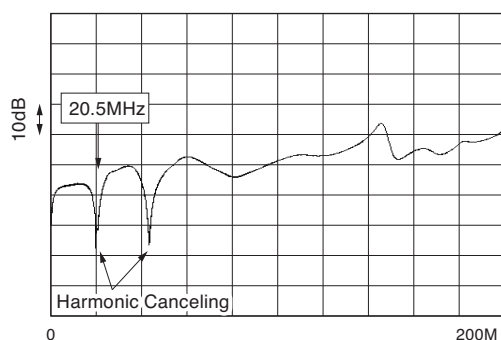
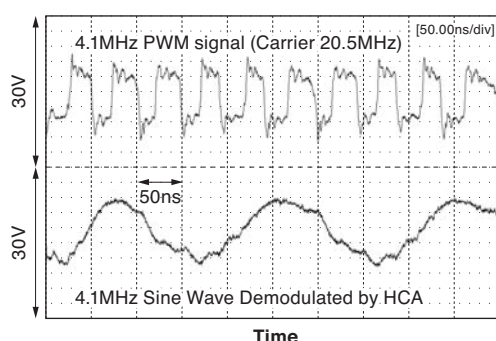


Fig. 11. HCA test circuit



(a) Frequency



(b) Waveform

Fig. 12. The characteristic of test circuit

## 5. Conclusion

The static and switching characteristics of 250 V/2.5 A 4H-SiC RESURF JFETs have been measured. It was confirmed that the JFET has fast switching characteristics; the turn-on and turn-off times are 2 ns and 2 ns, respectively. A demonstration of PWM demodulator with Harmonic Canceling switch Array using the JFETs was carried out. The input waveform, which is a pulse width modulated 20.5 MHz at 4.1 MHz sine wave, was demodulated at 4.1 MHz sine wave.

## 6. Acknowledgements

This work was supported in part by the New Energy and Industrial Technology Development Organization (NEDO) of Japan.

### References

- (1) H. Matsunami, ed., "Technology of semiconductor SiC and its application," the Nikkan Kogyo Shimbun (2003)
- (2) K. Arai and S. Yoshida, ed., "Basics and Application of SiC devices," Ohmsha (2003)
- (3) Fujikawa, Masuda, Tamaso, Shibata, Harada, Hatsukawa, Tokuda, Saegusa and Namikawa, SEI Technical Review No.61 (January 2006)
- (4) Tamaso, Sawada, Fujikawa, Harada, Shinkai, Tokuda, Masuda, Honaga, Itoh, Tsuno and Namikawa, SEI Technical Review No.66 (April 2008)
- (5) Tsuno, Itoh, Tamaso, Fujikawa, Sawada, Hatsukawa and Shiomi, SEI Technical Review No.178 (January 2011)

### Contributors (The lead author is indicated by an asterisk (\*).)

#### S. HATSUKAWA\*

- Assistant General Manager, Power Devise Development Division



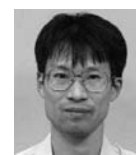
#### T. TSUNO

- Ph.D.,  
Manager, Power Devise Development Division



#### K. FUJIKAWA

- Ph.D.,  
Assistant General Manager, Design and Engineering Department Power Devise Development Division



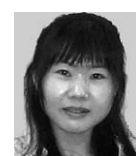
#### N. SHIGA

- Ph.D.,  
Chief Engineer, Power System R&D Labs.



#### T. WUREN

- Ph.D.,  
Toyoashi University of Technology



K. WADA

- Ph.D.,  
Toyohashi University of Technology



T. OHIRA

- Ph.D.,  
Toyohashi University of Technology

